TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOSIV)

TPCC8009

Lithium Ion Battery Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to a small and thin package
- Low drain-source ON-resistance:

 $R_{DS (ON)}$ = 5 m Ω (typ.) (V_{GS} = 10 V)

- Low leakage current: I_{DSS} = 10 μA (max) (V_{DS} = 30 V)
- Enhancement mode: V_{th} = 2.0 to 3.0 V (V_{DS} = 10 V, I_D = 0.2 mA)

Absolute Maximum Ratings (Ta = 25°C)

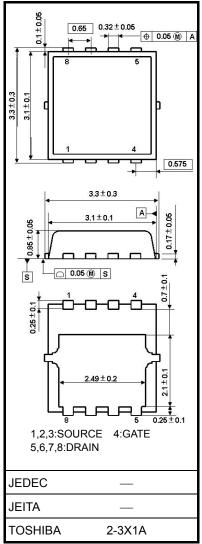
Characte	eristic	Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	30	V	
Drain-gate voltage (R	k _{GS} = 20 kΩ)	V _{DGR}	30	V	
Gate-source voltage		V _{GSS}	±20	V	
Drain ourrant	DC (Note 1)	۱ _D	24	Α	
Drain current	Pulsed (Note 1)	I _{DP}	72	А	
Drain power dissipati	on (Tc = 25°C)	PD	27	W	
Drain power dissipati	on (t = 10 s) (Note 2a)	PD	1.9	w	
Drain power dissipation (t = 10 s) (Note 2b)		PD	0.7	w	
Single-pulse avalance	he energy (Note 3)	E _{AS}	75	mJ	
Avalanche current		I _{AR}	24	A	
Channel temperature	1	T _{ch}	150	°C	
Storage temperature	range	T _{stg}	-55 to 150	°C	

Note: For Notes 1 to 3, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

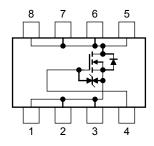
This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm



Weight: 0.02 g (typ.)

Circuit Configuration

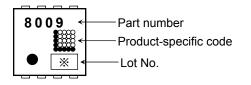


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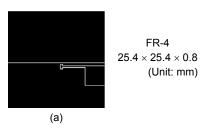
Thermal Characteristics

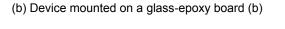
Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case (Tc = 25°C)	R _{th (ch-c)}	4.7	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R _{th (ch-a)}	66	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R _{th (ch-a)}	180	°C/W

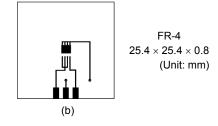
Marking (Note 4)



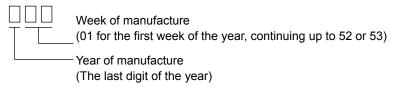
- Note 1: Ensure that the channel temperature does not exceed 150 $^{\circ}\text{C}.$
- Note 2: (a) Device mounted on a glass-epoxy board (a)







- Note 3: $V_{DD}=24$ V, $T_{ch}=25^{\circ}C$ (initial), $L=100~\mu H,~I_{AR}=24$ A
- Note 4: * Weekly code: (Three digits)



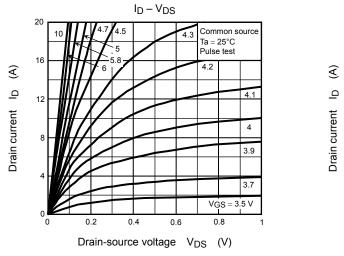
Electrical Characteristics (Ta = 25°C)

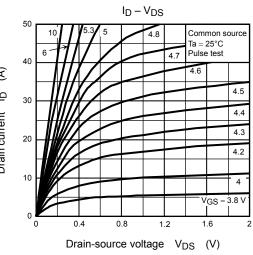
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I _{GSS}	$V_{GS}=\pm 16~V,~V_{DS}=0~V$			±10	μA
Drain cutoff curre	ent	IDSS	$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			10	μA
Drain agurag bra	ain-source breakdown voltage te threshold voltage ain-source ON-resistance ut capacitance verse transfer capacitance tput capacitance Rise time	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	30	_	_	V
Drain-source bre	akdown voltage	V (BR) DSX	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	10	_	_	v
Gate threshold ve	oltage	V _{th}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 0.2 \text{ mA}$	2.0	_	3.0	V
Drain-source ON-resistance		Deserve	$V_{GS} = 6 \text{ V}, \text{ I}_{D} = 12 \text{ A}$		7.2	11	-mΩ
		R _{DS (ON)}	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 12 \text{ A}$		5	7	
Input capacitance		C _{iss}	V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz	_	1270		pF
Reverse transfer capacitance		C _{rss}		_	230		
Output capacitance		C _{oss}		_	360		
Switching time	Rise time	tr	$V_{GS} \stackrel{10}{}_{0}V \prod_{V \in S} I_{D} = 12 \text{ A}$	_	6	_	- ns
	Turn-on time	ton			13	_	
	Fall time	t _f			6	_	
	Turn-off time	t _{off}		_	23	_	
Total gate charge (gate-source plus gate-drain)		Qg			26		nC
Gate-source charge 1		Q _{gs1}	V _{DD} ≈ 24 V, V _{GS} = 10 V, I _D = 24 A		5		
Gate-drain ("Miller") charge		Q _{gd}		—	8.2	—	

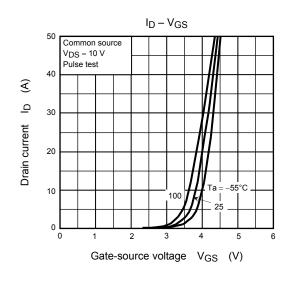
Source-Drain Ratings and Characteristics (Ta = 25° C)

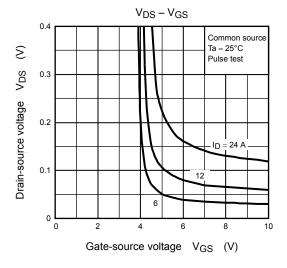
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit	
Drain reverse current	Pulse	(Note 1)	I _{DRP}	—	_	_	72	Α
Forward voltage (diode)			V _{DSF}	$I_{DR} = 24 \text{ A}, V_{GS} = 0 \text{ V}$	_		-1.2	V

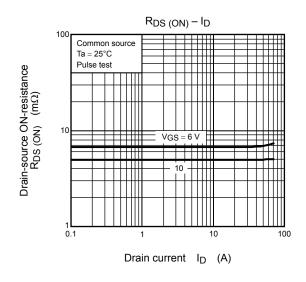
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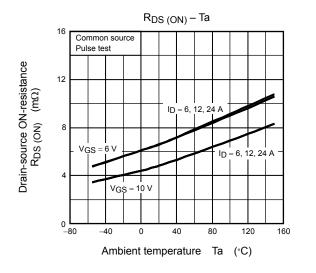


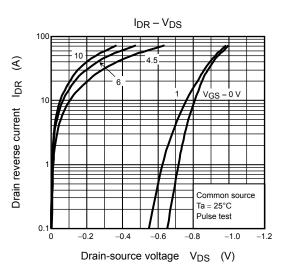


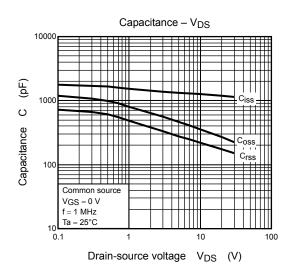


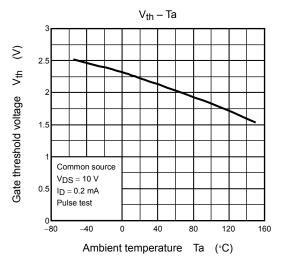


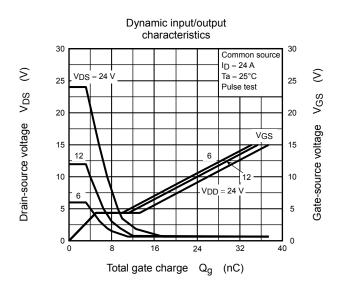
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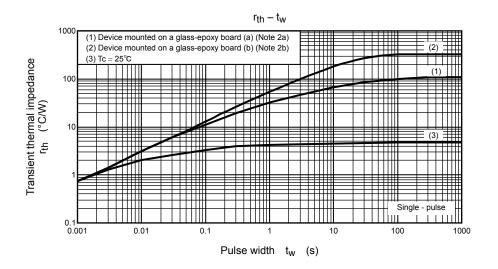


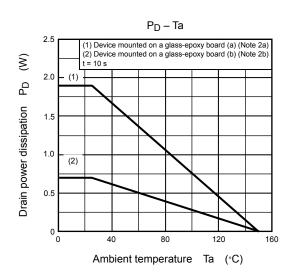


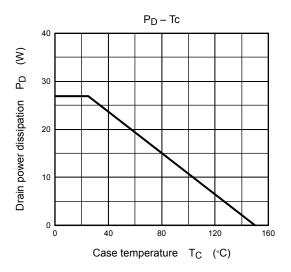


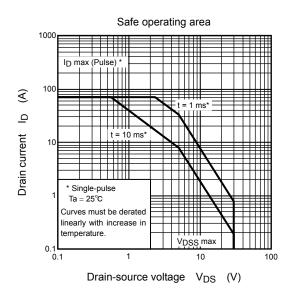












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